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Correction: Designing high-performance infrared optoelectronic materials: indium-site substitution in LiInSe_2 with Al, Ga, Sn, and Sb

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The authors regret that the affiliations for Yanan Zhang and Suwen Han were incorrectly shown in the original manuscript. The correct list of affiliations is as shown here.

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

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